

U.S.S.N. 10/606,823

IN THE CLAIMS

Please cancel Claims 24,31 and 34-38 without prejudice.

Please amend Claims 25 and 27-30.

U.S.S.N. 10/606,823

Listing of Claims

Claims 1- 24 (canceled)

25. (currently amended) The method of claim ~~24~~ 39, further comprising exposing the defectively exposed portion to the second mask part a second time.

26. (previously presented) The method of claim 25, further comprising exposing the defectively exposed portion to the second mask part a third time.

27. (currently amended) The method of claim ~~24~~ 39, further comprising exposing the defectively exposed portion to the second mask part one or more additional times.

28. (currently amended) The method of claim ~~24~~ 39 further comprising exposing the defectively exposed portion to the second, a third and other additional mask parts one or more additional times.

29. (currently amended) The method of claim ~~24~~ 39, wherein the first mask part comprises a layout for a semiconductor device that is at least partially defective, and the second mask part

U.S.S.N. 10/606,823

comprises the layout for the semiconductor device that is at least substantially free from defects or with defects at different locations.

30. (currently amended) The method of claim ~~24~~ 39, wherein exposing the semiconductor wafer to the first mask part and exposing the defectively exposed portion to the second mask part comprise a lithographic semiconductor fabrication process.

31. (cancelled)

32. (currently amended) The method of claim ~~24~~ 39, wherein the first mask part and the second mask part are on a same photomask.

33. (currently amended) The method of claim ~~24~~ 39, wherein the first mask part and the second mask part are on different photomasks.

Claims 34-38 (cancelled)

39. (previously presented) A method for repairing a defectively exposed semiconductor wafer comprising:

exposing a semiconductor wafer to a first mask part that is

U.S.S.N. 10/606,823

at least partially defective to form a defectively exposed portion; and,

exposing the defectively exposed portion to a second mask part corresponding to the first mask part and that is at least substantially free from defects or with defects at different locations to at least partially repair said defectively exposed portion.